

60V N-Channel MOSFET



SOT-363

Pin Definition:

654 67 1. Source 2 6. Drain 2 2. Gate 2 5. Gate 1

3. Drain 1 4. Source 1

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (mA)
60	2 @ V _{GS} = 10V	300
	4 @ V _{GS} = 4.5V	200

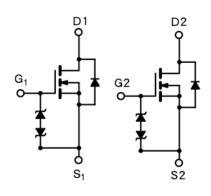
Features

- Low On-Resistance
- ESD Protection
- High Speed Switching
- Low Voltage Drive

Ordering Information

Part No.	Package	Packing
TSM2N7002KDCU6 RF	SOT-363	3Kpcs / 7" Reel

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	60	V	
Gate-Source Voltage		V_{GS}	±20	V	
Drain Current	Continuous @ T _A =25°C	I _D	300	mA	
	Pulsed	I _{DM}	800		
Drain Reverse Current	Continuous @ T _A =25°C	I _{DR}	300	mA	
	Pulsed	I _{DMR}	800		
Maximum Power Dissipation		P _D	300	mW	
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T _L	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	RΘ _{JA}	625	°C/W

1/6

Notes:

- a. Pulse width ≤300us, Duty cycle ≤2%
- b. When the device is mounted on a glass epoxy board with area measuring 1 x 0.75 x 0.62 inch.
- c. The power dissipation of the package may result in a continuous drain current.

Version: B09



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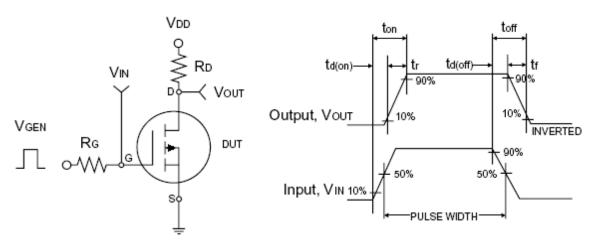
Pb Rohs COMPLIANCE

Electrical Specifications (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit	
Static	Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	60			V	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.0	1.5	2.5	V	
Gate Body Leakage	V_{GS} =±20V, V_{DS} =0V	I_{GSS}	1		±10	uA	
Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	I _{DSS}	1		1.0	uA	
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 300 \text{mA}$	J	1	1.2	2	Ω	
Drain-Source On-State Resistance	V_{GS} =4.5V, I_{D} =100mA	$R_{DS(ON)}$	1	2	4		
Forward Transconductance	$V_{DS} = 10V, I_{D} = 200 \text{mA}$	g _{fs}	100			mS	
Diode Forward Voltage	I _S =300mA, V _{GS} =0V	V_{SD}	-	0.8	1.4	V	
Dynamic ^b							
Total Gate Charge	V_{DS} =10V, I_{D} = 250mA, V_{GS} =4.5V	Q_g		0.4	0.6	nC	
Input Capacitance	\/ - 05\/ \/ - 0\/	C _{iss}		30			
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		6		pF	
Reverse Transfer Capacitance	1 - 1.0IVINZ	C_{rss}	1	2.5			
Switching ^c							
Turn-On Delay Time	$V_{DD} = 30V, R_G = 10\Omega$	t _{d(on)}	-		25	20	
Turn-Off Delay Time	$I_D = 200 \text{mA}, V_{GEN} = 10 \text{V},$	$t_{d(off)}$			35	nS	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

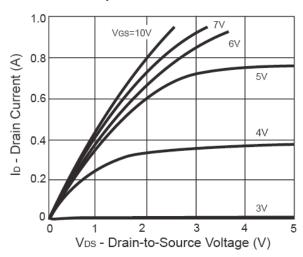


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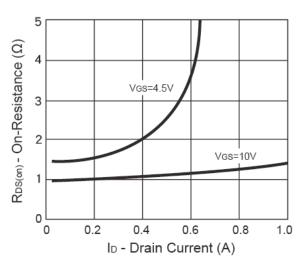
Pb Rohs COMPLIANCE

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

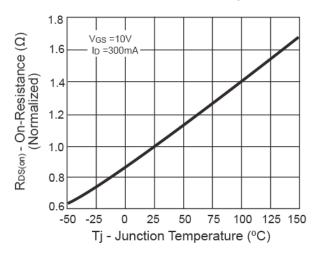
Output Characteristics



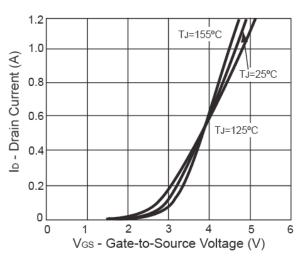
On-Resistance vs. Drain Current



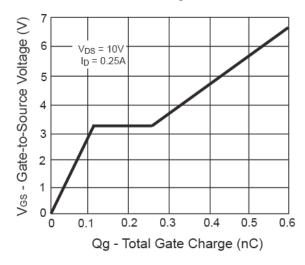
On-Resistance vs. Junction Temperature



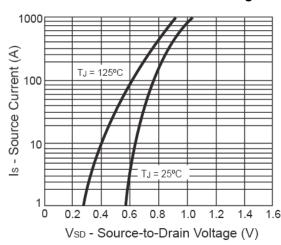
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



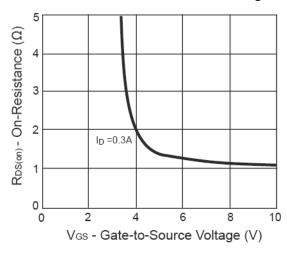


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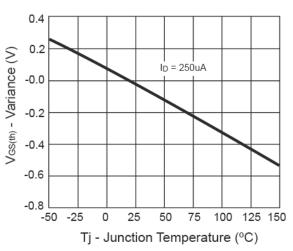


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

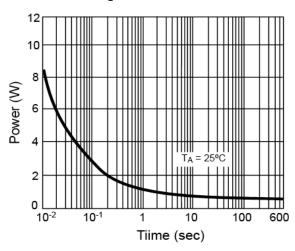
On-Resistance vs. Gate-Source Voltage



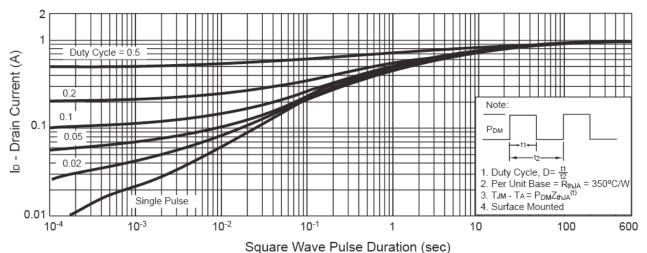
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

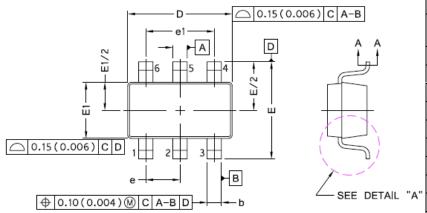




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SOT-363 Mechanical Drawing



SOT-363 DIMENSION				
DIM MILLIME		ETERS INCHES		HES
DIIVI	MIN	MAX	MIN	MAX.
Α	0.80	1.10	0.031	0.043
A1	0	0.10	0	0.004
A2	0.80	1.00	0.031	0.040
b	0.15	0.30	0.006	0.012
b1	0.15	0.25	0.006	0.010
С	0.08	0.22	0.003	0.009
c1	0.08	0.20	0.003	0.008
D	1.90	2.10	0.074	0.084
Е	2.00	2.20	0.078	0.086
E1	1.15	1.35	0.045	0.055
е	0.65 BSC		0.025	BSC
e1	1.30 BSC		0.051	BSC
L	0.26	0.46	0.010	0.018
θ	0°	8°	0°	8°
θ1	4°	10°	4°	10°

	A A A	SEATING PLANE
0.10(0.004)C	A -	С



TSM2N7002KD 60V N-Channel MOSFET

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